



2SB817

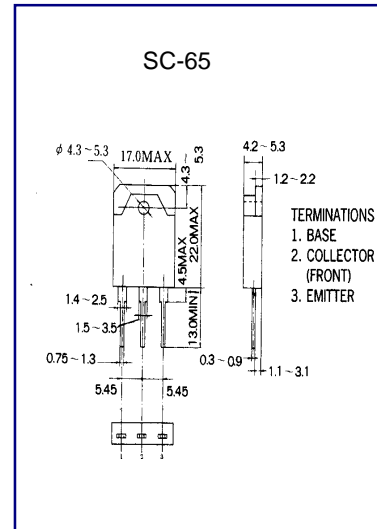
PNP PLANAR SILICON TRANSISTOR

AUDIO POWER AMPLIFIER DC TO DC CONVERTER

- High Current Capability
- High Power Dissipation
- Complementary to 2SD1047

ABSOLUTE MAXIMUM RATING (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-160	V
Collector-Emitter Voltage	V _{CEO}	-140	V
Emitter-Base voltage	V _{EBO}	-6	V
Collector Current (DC)	I _C	-12	A
Collector Dissipation	P _C	100	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV _{CB0}	I _C =-5 mA I _E =0	-160			V
Collector Emitter Breakdown Voltage	BV _{CEO}	I _C =-10 mA R _{BE} =∞	-140			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E =-5mA I _C =0	-6			V
Collector Cutoff Current	I _{CB0}	V _{CB} =-60V I _E =0			-0.1	mA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V I _C =0			-0.1	mA
*DC Current Gain	h _{FE1}	V _{CE} =-5V I _C =-1A	55		160	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =-5A I _B =-0.5A			-25	V